

REMARKS

Favorable reconsideration of this application is requested in view of the above amendments and the following remarks. Claims 2, 3, 7, 9, 10, 14, 25, and 28 are amended. The revisions to these claims are fully supported by the specification and the previously presented claims. Claims 23, 24, 26, and 27 are canceled without prejudice to or disclaimer of the subject matter recited therein.

Claims 2, 3, 7, 9, 10, 14, 15, 17, 25, and 28 are pending, with claims 2, 3, 9, and 10 being independent.

Claim rejections - 35 U.S.C. § 103

Claims 2, 3, 7, 9, 10, 14, 15, 17, and 23-28 stand rejected as being unpatentable over U.S. Patent No. 5,693,569 (Ueno). Applicant respectfully traverses this rejection.

Claim 2 is directed to a semiconductor element. A semiconductor body is made of silicon carbide. A plurality of the field-effect transistors are arranged, and the metal electrodes of the Schottky diode are provided so as to extend between the transistors. The metal electrodes are disposed on a flat surface.

By this arrangement, the semiconductor element is capable of quickly responding from an on-state to an off-state, without increasing the size of the element. *See, e.g.*, page 7, lines 18-31. In particular, by forming metal electrodes between the transistors, the present invention is capable of providing a highly compact structure. Furthermore, by disposing the metal electrodes on a flat surface, a minimum amount of area is required between the transistors, further allowing for a compact structure. The flat surface also minimizes the distance between second conductivity type semiconductors, which allows the breakdown voltage of the semiconductor element to be increased. *See, e.g.*, page 7, lines 32-37.

Ueno is directed to method of forming a silicon carbide trench MOSFET with a Schottky electrode. However, Ueno does not disclose a structure where metal electrodes of a Schottky diode are provided so as to extend between a plurality of field-effect transistors. Nor does Ueno teach or suggest that the metal electrodes are disposed on a flat surface. In contrast, Ueno discloses that the Schottky electrode **21** is disposed on an uneven surface that is broken by trench

5. *See, e.g.*, Figure 1. Accordingly, Ueno does not teach or suggest the structure recited by claim 2, nor does Ueno provide the benefits resulting from such a structure.

Ueno does not teach or disclose at least the above-described features. Applicant therefore submits that claim 2 is allowable over the cited reference.

Independent claims 3, 9, and 10 also recite the features identified above with respect to claim 2. Therefore, claims 3, 9, and 10 are believed allowable over the cited reference for at least the same reasons provided above with respect to claim 2.

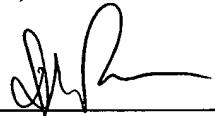
Claims 7, 14, 15, 17, 25, and 28 depend from one of claims 2, 3, 9, and 10. Therefore, each of those claims is believed allowable for at least the reason that it is dependent upon an allowable base claim.

In view of the above, favorable reconsideration in the form of a notice of allowance is requested.

Respectfully submitted,

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